

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the present application.

Listing of Claims:

Claim 1 (currently amended): A ceramic susceptor for semiconductor manufacturing equipment, the ceramic susceptor comprising:

a ceramic substrate, one side thereof having a wafer-retaining face;

a resistive heating element provided either superficially or interiorly in said substrate; and

a recess formed in said wafer-retaining face with room to carry a semiconductor manufacturing wafer, said recess ~~being contoured either so that its~~ including a perimetric wall and a substantially planar bottom face, and being shaped such that the perimetric wall meets ~~[[its]] the~~ bottom face to form an angle of ~~over~~ greater than 90° and less than 170° ~~or less, or so that its perimetric wall and its bottom face join in a bottom portion circumferential verge having a curvature of 0.1 mm or more.~~

Claim 2 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, wherein said ceramic substrate is made of at least one selected from the group consisting of: aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 3 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, wherein said resistive heating element is

made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 4 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 2, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 5 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 6 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 2, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 7 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 3, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 8 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 4, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 9 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 1, wherein said recess is ~~contoured both~~ further shaped so that ~~its perimetric wall meets its bottom face to form an angle of over 90° and 170° or less, and so that its~~ the perimetric wall and ~~its~~ the bottom face

join in a bottom-portion circumferential ~~rim~~verge having a curvature of 0.1 mm or more.

Claim 10 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said ceramic substrate is made of at least one selected from the group consisting of: aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 11 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 12 (currently amended): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 10, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 13 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 14 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 10, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 15 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 11, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 16 (original): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 12, further comprising a plasma electrode disposed either superficially or interiorly in said ceramic substrate.

Claim 17 (new): A ceramic susceptor for semiconductor manufacturing equipment, the ceramic susceptor comprising:

- a ceramic substrate, one side thereof having a wafer-retaining face;
- a resisted heating element provided either superficially more interiorly in said substrate; and
- a recess formed in said wafer-retaining face with room to carry a semiconductor manufacturing wafer, the recess including a perimetric wall and a bottom face, the perimetric wall and the bottom face joining in a circumferential verge having a radius of curvature of a 0.1 mm or more.

Claim 18 (new): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said ceramic substrate is made of at least one selected from the group consisting of: aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 19 (new): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 9, wherein said resistive heating element is made

from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 20 (new): A semiconductor-manufacturing-equipment ceramic susceptor as set forth in claim 10, wherein said resistive heating element is made from at least one selected from the group consisting of: tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.